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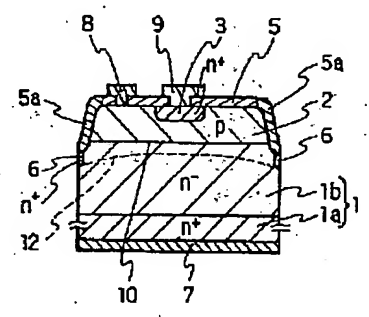
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(54) **SEMICONDUCTOR DEVICE AND ITS MANUFACTURE**

(57) Abstract

**PURPOSE:** To provide a mesa semiconductor device whose breakdown voltage can be increased without making the chip size too large and the depth of a recessed groove for forming the device in a mesa too deep.

**CONSTITUTION:** A semiconductor device in which a semiconductor layer 2 having a second conductivity is separated in a mesa is manufactured by forming a p-n junction 10 by providing the semiconductor layer 2 for forming a semiconductor element on a semiconductor layer 1 having a first conductivity and a recessed groove deeper than the p-n junction in the semiconductor layer 2. In the semiconductor device, a channel stopper 6 which has the same conductivity as that of the semiconductor layer 1 has and contains high concentration impurity is provided on the bottom of the recessed groove.



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